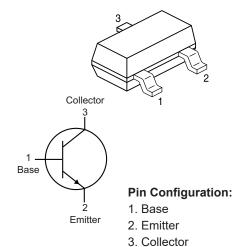
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Features

- For general AF applications
- · High current gain
- · Low collector-emitter saturation voltage
- Complementary types: BCW67, BCW68 (PNP)



Applications

- · General purpose medium power amplifier
- · Switching application

Maximum Ratings

Parameter	Symbol	Value	Unit	
Collector - Base Voltage	Vсво	45		
Collector - Emitter Voltage	VCEO	75	V	
Emitter - Base Voltage	VEBO	5		
DC Collector Current	Ic	-1	А	
Collector Current Continuous	Ic	800	mA	
Collector Dissipation	Pc	330	mW	
Junction and Storage Temperature	ТJ, Tsтg	-65 to +150	°C	

Electrical Characteristics (T_A = 25°C unless otherwise noted)

Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Collector - Base Breakdown Voltage	V _{(BR)CBO}	Ic=10μA, IE=0	75			
Collector - Emitter Breakdown Voltage	V _{(BR)CEO}	Ic=10mA, Iв=0	45			V
Emitter - Base Breakdown Voltage	V _{(BR)EBO}	IE=10μA, Ic=0	5			
Collector Cut-Off Current	I _{CBO}	Vcb=45V, IE=0			20	- A
Emitter Cut-Off Current	I _{EBO}	VEB=4V, IC=0			20	nA
DC Current Gain		V _{CE} =10V, I _C =100μA	50 80	-	-	
	hFE	V _{CE} =1V, I _C =10mA 120		-	-	-
		V _{CE} =1V, I _C =100mA	160 250	-	400 630	





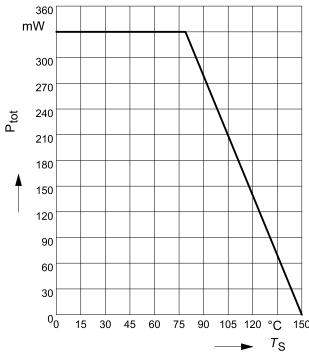
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Collector - Emitter Saturation Voltage	VCE(sat)	I _C =-100mA, I _B =10mA I _C =-500mA, I _B =50mA	-	-	0.3 0.7	V
Base Emitter Saturation Voltage	V _{BE} (sat)	I _C =100mA, I _B =10mA I _C =500mA, I _B =50mA	-	1	1.25 2	V
Transition Frequency	fτ	V _{CE} =5V, I _C =50mA f=20MHz	-	170	-	MHz

Thermal Characteristics

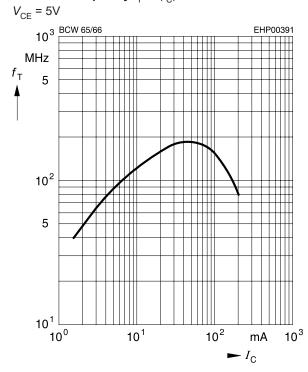
Parameter	Symbol	Value	Unit
Power Dissipation	Pb	330	mW
Thermal Resistance Junction-to-Air *	RθJA	395	°C/W
Thermal Resistance Junction-to-Case *	RθJC	218	°C/W
Thermal Resistance Junction-to-Lead *	RθJL	191	°C/W
Operating Junction temperature	TJ	-55 to +150	°C
Storage Temperature Range	Тѕтс	-55 10 +150	

Note: * The data tested by surface mounted on a 15mm×15mm×1mm FR4-epoxy P.C.B





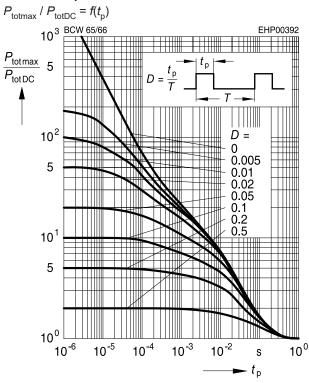
Transition frequency $f_T = f(I_C)$



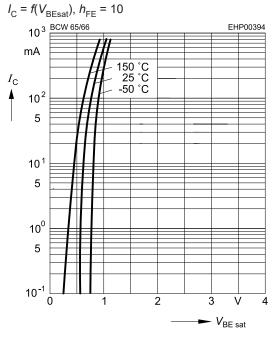


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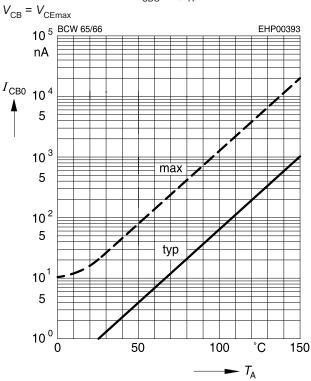
Permissible pulse load



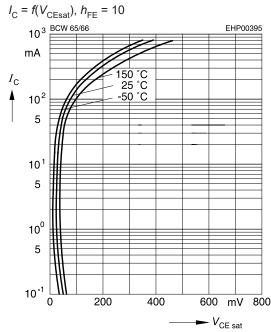
Base-emitter saturation voltage



Collector cutoff current $I_{CBO} = f(T_A)$



Collector-emitter saturation voltage

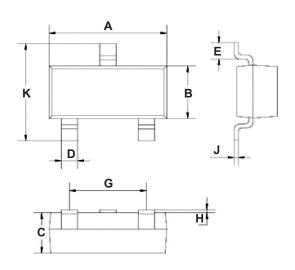






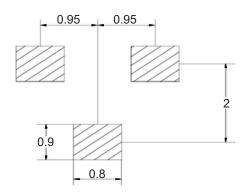
Package Outline

Plastic Surface Mounted Package



Dimensions	Min.	Max.	
А	2.85	2.95	
В	1.25	1.35	
С	1 Typical		
D	0.4 Typical		
E	0.35	0.48	
G	1.85	1.95	
Н	0.02	0.1	
J	0.1 Typical		
K	2.35	2.45	

Soldering Footprint



Part Number Table

Description	Part Number		
Transistor, NPN, 0.8A, 45V, SOT-23	BCW66H		

Dimensions: Millimetres

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